



FOURTH SEMESTER BTECH. (E & C) DEGREE END SEMESTER EXAMINATION

JUNE 2022

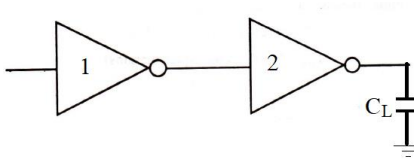
SUBJECT: VLSI DESIGN (ECE - 2254)

TIME: 3 HOURS

MAX. MARKS:50

Instructions to candidates

- Answer **ALL** questions.
- Missing data may be suitably assumed.
- Graph sheet will be provided

Q. No.	Questions	M*	C*	A*	B*										
1A.	<p>Two Pseudo NMOS inverters are cascaded to drive a capacitive load of $C_L = 16C_g$ as shown in the Fig. Q 1A. Calculate the pair delay in terms of τ for the inverter geometry indicated in the figure.</p> <div><table><tr><th>Inverter-1</th><th>Inverter-2</th></tr><tr><td>$L_{PU}=6\lambda$</td><td>$L_{PU}=12\lambda$</td></tr><tr><td>$W_{PU}=2\lambda$</td><td>$W_{PU}=4\lambda$</td></tr><tr><td>$L_{PD}=2\lambda$</td><td>$L_{PD}=4\lambda$</td></tr><tr><td>$W_{PD}=2\lambda$</td><td>$W_{PD}=4\lambda$</td></tr></table><p style="text-align: center;">Fig. Q1A</p></div>	Inverter-1	Inverter-2	$L_{PU}=6\lambda$	$L_{PU}=12\lambda$	$W_{PU}=2\lambda$	$W_{PU}=4\lambda$	$L_{PD}=2\lambda$	$L_{PD}=4\lambda$	$W_{PD}=2\lambda$	$W_{PD}=4\lambda$	4	4	1,2	3
Inverter-1	Inverter-2														
$L_{PU}=6\lambda$	$L_{PU}=12\lambda$														
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$W_{PD}=2\lambda$	$W_{PD}=4\lambda$														
1B.	Implement 3-input NAND gate using BiCMOS logic.	3	2	1	3										
1C.	Describe the working of 4×4 cross bar switch with the help of neat diagram and list its disadvantages.	3	5	1	2										
2A.	Draw the layout of depletion load NMOS inverter using λ based design rule.	4	4	1,1 2	2										
2B.	<p>Show that a full adder block can be used as subsystem to implement the following functions</p> <p>i. 2 input XNOR</p> <p>ii. 2 input OR</p> <p>iii. 2 input AND</p>	3	5	1,1 2	2										
2C.	Describe the working of n-bit parity generator using structured approach.	3	5	1	1										
3A.	Describe the fabrication of P-channel Enhancement MOSFET with the help of neat diagram.	4	3	1	1										

3B.	Explain the working on non-inverting super buffer.	3	2	1	1
3C.	Implement $Z = \overline{(A.B + C).D}$ using CMOS logic.	3	2	1	3
4A.	Describe the problem associated with N-Well CMOS process and its solution.	4	3	1	1
4B.	Describe the fabrication of Enhancement MESFET with the help of neat diagram.	3	5	1	1
4C.	Describe the working (Read and Write operation) of 6-T SRAM.	3	2	1	1
5A.	<p>Give the circuit implementation of following multiple output function using Pseudo-NMOS PLA.</p> $F=AB+A'B'C$ $G= A \text{ XOR } B$ $H=AB+BC+AC$	4	5	1	3
5B.	<p>Implement the given words using NAND ROM and draw its stick diagram.</p> $\begin{bmatrix} w0 \\ w1 \\ w2 \\ w3 \end{bmatrix} = \begin{bmatrix} 0 & 1 & 0 & 1 \\ 1 & 1 & 0 & 0 \\ 1 & 1 & 1 & 1 \\ 0 & 0 & 0 & 0 \end{bmatrix}$	3	2	1	3
5C.	Implement N-Input NOR gate using dynamic CMOS logic.	3	2	1	3

M*--Marks, C*--CLO, A*--AHEP LO, B* Blooms Taxonomy Level